

6. A dual band RF tuning circuit as recited in claim 1, and further comprising: a first resistance connected across a gate of the switching transistor, the source of band control voltage being connected to a dividing point of the first resistance, and the conducting drain and source nodes of the switching transistor being in series connection with the second impedance element to open-circuit the second impedance element.

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8. A dual band RF tuning circuit as recited in claim 6, wherein the first resistance is a current blocking resistance in parallel connection with the conducting drain and source nodes of the switching transistor, and the source of band control voltage is connected through a second resistor to the dividing point of the first resistance.

9. A dual band RF tuning circuit comprising:
a first inductance impedance element and a second inductance impedance element between an RF input port and an RF output port,
the tuning circuit being tuned by the first and second inductance impedance elements to receive a first RF signal and to provide the first RF signal at the output port,
the tuning circuit being tuned by the first inductance impedance element alone to receive a second RF signal and to provide the second RF signal at the output port,
a first switching transistor being switched on and off by changing its bias voltage,
a band control voltage source connected to the first switching transistor to change its bias voltage,

the first switching transistor having conducting drain and source nodes connected to the second inductance impedance element to short the second inductance impedance element, which tunes the tuning circuit by the first inductance impedance element,

a first capacitance impedance element and a second capacitance impedance element between the RF input port and the RF output port,

the tuning circuit being tuned by the first and second capacitance impedance elements to receive a first RF signal and to provide the first RF signal at the output port,

the tuning circuit being tuned by the first capacitance impedance element alone to receive a second RF signal and to provide the second RF signal at the output port,

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Cont' a second switching transistor being switched on and off by changing its bias voltage,

the band control voltage source connected to the second switching transistor to change its bias voltage, and

the second switching transistor having conducting drain and source nodes connected to the second capacitance impedance element to short the second capacitance impedance element, which tunes the tuning circuit by the first capacitance impedance element.

10. A dual band RF tuning circuit as recited in claim 9, and further comprising: the conducting drain and source nodes of the first switching transistor being in parallel connection with the second inductance impedance element to short the second inductance impedance element.

11. A dual band RF tuning circuit as recited in claim 9, and further comprising: a first resistance connected to a gate of the second switching transistor, and the source of band control voltage being connected to a dividing point of the first resistance, and the conducting drain and source nodes of the second switching transistor being in series connection with the second capacitance impedance element to short the second capacitance impedance element.

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12. A dual band RF tuning circuit as recited in claim 11, wherein the first resistance is a current blocking resistance in parallel connection with the conducting drain and source nodes of the second switching transistor, and the source of band control voltage is connected through a second resistor to a dividing point of the first resistance.

13. A dual band RF tuning circuit as recited in claim 9, and further comprising: the first switching transistor is an EFET transistor, and a further resistor is referenced to ground and is connected at the gate to the EFET transistor.

14. A dual band RF tuning circuit as recited in claim 9, and further comprising: the output of the RF tuning circuit being supplied to an amplifier at an input side of a second dual band RF tuning circuit.

Please add the following new claims.

16. (New) The dual band RF tuning circuit as recited in claim 1, wherein the switching

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transistor is a MESFET.

17. (New) The dual band RF tuning circuit as recited in claim 16, wherein said switching transistor is integrally formed with the tuning circuit in a single integrated circuit.

18. (New) The dual band RF tuning circuit as recited in claim 1, wherein said switching transistor is integrally formed with the tuning circuit in a single integrated circuit.

19. (New) The dual band RF tuning circuit as recited in claim 9, wherein the first switching transistor is a MESFET.

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20. (New) The dual band RF tuning circuit as recited in claim 9, wherein the second switching transistor is integrally formed with the tuning circuit in a single integrated circuit.

Concl
21. (New) A dual band RF tuning circuit comprising;
a first dual band RF tuning circuit as recited in claim 9;
an amplifier coupled to receive an output of the first dual band RF tuning circuit; and
a second dual band RF tuning circuit as recited in claim 9 coupled to receive an output of the amplifier.